Form PTO 1449 (Modified)	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY DOCKET NO. 250386US2	SERIAL NO. 10/799,780 New Application
LIST OF REFERENCES CITED BY APPLICANT		APPLICANT Satoshi INABA, et al.	
		FILING DATE Herewith	GROUP 2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
TH	AA	6,525,403	02/25/03	Satoshi INABA, et al.	—	—	—
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES	TRANSLATION NO
TH	AO	7-202146	08/04/95	Japan (with English Abstract)		x
	AP					
	AQ					
	AR					
	AS					
	AT					
	AU					
	AV					

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)

TH	AW	Yang-Kyu CHOI, et al., "Sub-20nm CMOS FinFET Technologies", INTERNATIONAL ELECTRON DEVICES MEETING (IEDM) TECH. DIG., December 2001, pgs. 421-424
TH	AX	Bin YU, et al., "FinFET Scaling to 10nm Gate Length", INTERNATIONAL ELECTRON DEVICES MEETING (IEDM) TECH. DIG., December 2002, pgs. 251-254
	AY	
	AZ	☐ Additional References sheet(s) attached

Examiner Tue-Tue HO — Date Considered NOV 2005

*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.